

Lattice Anharmonicity in BiS₂-Based Layered Superconductor RE(O,F)BiS₂ (RE = La, Ce, Pr, Nd)

Fysol Ibna Abbas^{1,2}, Kazuhisa Hoshi¹, Aichi Yamashita¹, Yuki Nakahira¹, Yosuke Goto¹, Akira Miura³, Chikako Moriyoshi⁴, Yoshihiro Kuroiwa⁴, Kensei Terashima⁵, Ryo Matsumoto^{5,6}, Yoshihiko Takano⁵, and Yoshikazu Mizuguchi^{1*}

¹ *Department of Physics, Tokyo Metropolitan University, 1-1, Minami-osawa, Hachioji 192-0397, Japan*

² *Department of Electrical & Electronic Engineering, City University, Khagan, Birulia, Savar, Dhaka-1216, Bangladesh*

³ *Faculty of Engineering, Hokkaido University, Kita 13 Nishi 8, Sapporo 060-8628, Japan*

⁴ *Graduate School of Advanced Science and Engineering, Hiroshima University, Higashihiroshima, Hiroshima, 739-8526, Japan*

⁵ *International Center for Materials Nanoarchitectonics (MANA), National Institute for Materials Science, Tsukuba, Ibaraki 305-0047, Japan*

⁶ *International Center for Young Scientists (ICYS), National Institute for Materials Science, Tsukuba, Ibaraki 305-0047, Japan*

6

(Received ***, 2022)

Abstract

We studied Grüneisen parameter (γ_G) to investigate lattice anharmonicity in a layered BiS₂-based superconductor system REO_{1-x}F_xBiS₂ (RE = La, Ce, Pr, Nd), where in-plane chemical pressure was tuned by substituting the RE elements. With increasing in-plane chemical pressure, bulk modulus remarkably increases, and a high γ_G is observed for RE = Nd. The dependence of γ_G on in-plane chemical pressure exhibits a good correlation with T_c , and a higher T_c is achieved when γ_G is large for RE = Nd. In addition, γ_G shows a slight decrease by a decrease of F concentration (x) in REO_{1-x}F_xBiS₂. Our results show that the anharmonic vibration of Bi along the c -axis is present in REO_{1-x}F_xBiS₂, and the enhancement of the anharmonicity is positively linked to superconducting T_c and pairing mechanisms.

1. Introduction

The presence of lattice anharmonicity has been one of the important issues in superconductors with a high transition temperature (T_c) and exotic pairing mechanisms. For example, anharmonicity and structural instability is essential parameter for T_c in A15-type superconductors [1] and rattling materials [2,3]. In addition, anharmonicity has been observed in MgB_2 [4] and superhydrides (superconductors with hydrogen-rich compositions) [5]. Although anharmonic vibration is positively linked to superconductivity in [2,3,6], a theoretical study on a superhydride suggested that giant anharmonicity suppresses T_c in the material [7]. Therefore, control of anharmonicity is one of key factors for designing new superconductors and improving their superconducting properties. In this study, we investigate the relationship between superconductivity and anharmonicity in a BiS_2 -based layered superconductor via the estimation of Grüneisen parameter (γ_G).

The BiS_2 -based superconductors, which are a layered superconductor family having an alternate stacking structure of blocking layer and conducting layer (BiS_2 layer), were discovered in 2012, and many analogous BiS_2 -based superconductors have been synthesized [8–19]. BiS_2 layers are essential to superconductivity [20–22], and superconductivity is induced after carrier doping and optimization of crystal structure [17,23,24]. In particular, the importance of in-plane chemical pressure effect [25], which suppresses local structural disorder (local distortion) in BiS_2 layers [25–30], has been found. One of the origins of the local disorder in the BiS_2 layers is the presence of Bi lone pairs [27]. In addition, structural instability has been predicted theoretically [31]. Hence, the relationship between superconductivity and structural instability would be a key factor, but the point has not been experimentally studied. On the mechanisms of superconductivity, recent experimental and theoretical works indicated the possibility of unconventional superconductivity with an anisotropic superconducting gap structure [32–36]. Furthermore, by focusing on the suppression of the local disorder and the improvement of superconducting properties by in-plane chemical pressure [25], we have revealed some evidences of unconventional pairing in $\text{La}(\text{O},\text{F})\text{Bi}(\text{S},\text{Se})_2$ and $\text{Bi}_4\text{O}_4\text{S}_3$ where in-plane chemical pressure is high enough for the suppression of local disorder: the absence of isotope effects, nematic superconductivity, and high upper critical fields [38–42].

Motivated by the background knowledges on BiS_2 -based superconductivity, we here focus on the relationship between superconductivity and lattice anharmonicity in $\text{REO}_{1-x}\text{F}_x\text{BiS}_2$ (RE = La, Ce, Pr, Nd). In a related $\text{LaOBi}(\text{S},\text{Se})_2$ system, which shows high thermoelectric properties [43,44], evolution of anharmonic vibration in BiS_2 layers has been detected by

inelastic neutron scattering (INS) [45]. In the system, low thermal conductivity was explained by the enhanced anharmonicity. In addition, we recently analyzed anharmonicity in LaOBi(S,Se)_2 by estimating γ_G and reproduced the trend found in the INS [46]. Since anharmonicity is enhanced by in-plane chemical pressure in LaOBi(S,Se)_2 by Se substitution, we investigate the dependences of γ_G on in-plane chemical pressure tuned by RE ionic radii in $\text{REO}_{1-x}\text{F}_x\text{BiS}_2$ in this paper. As a main conclusion, we show that anharmonicity is enhanced by in-plane chemical pressure and exhibits a positive correlation with T_c in $\text{REO}_{1-x}\text{F}_x\text{BiS}_2$.

2. Experimental details

2.1 methods

Polycrystalline samples were synthesized by solid-state reaction as described in Refs. 9 and 26. Synchrotron X-ray diffraction (SXR) experiments were performed at the beamline BL02B2, SPring-8 at a wavelength of 0.49559 Å (proposal No. 2017B1211). The SXR experiments were performed with a sample rotator system at room temperature; the diffraction data were collected using a high-resolution one-dimensional semiconductor detector (multiple MYTHEN system [47]) with a step size of $2\theta = 0.006^\circ$. The temperature of the sample was controlled by nitrogen gas. The crystal structure parameters were refined using the Rietveld method using RIETAN-FP [48]. The image of schematic models of the crystal structures was produced using VESTA [49]. Specific heat was measured by relaxation method using a Physical Property Measurement System (PPMS, Quantum Design). Longitudinal sound velocity (v_L) of the sample was measured using an ultrasonic thickness detector (Satotech-2000C). For sound velocity measurements, the obtained samples were densified using high-pressure synthesis method with a 180-ton cubic-anvil system with a pressure of ~1.5 GPa and an annealing temperature of ~400 °C for 15 min.

2.2 Grüneisen parameter

γ_G of samples was calculated using the following formula [45,50];

$$\gamma_G = \frac{\beta_V B V_{\text{mol}}}{C_V} \quad (1)$$

, where β_V , B , V_{mol} , and C_V are volume thermal expansion coefficient, bulk modulus, molar volume, and specific heat, respectively. The parameters needed for the estimation of γ_G are calculated as follows (formula 2–5). In the formulas, dV/dT , ρ , v_L , v_S , v_m , θ_D , h , k_B , n , N_A , and M denote temperature gradient of lattice volume, density of the material, longitudinal sound velocity, shear sound velocity, average sound velocity, Debye temperature, Plank's constant,

Boltzmann's constant, number of atoms in the molecule (formula unit), Avogadro's constant, and the molecular weight (per formula unit).

$$\beta_V = \frac{1}{V(300\text{ K})} \frac{dV}{dT} \quad (2)$$

$$B = \rho \left(v_L^2 - \frac{4}{3} v_S^2 \right) \quad (3)$$

$$\theta_D = \left(\frac{h}{k_B} \right) \left[\frac{3n}{4\pi} \left(\frac{N_A \rho}{M} \right) \right]^{\frac{1}{3}} v_m \quad (4)$$

$$v_m = \left[\frac{1}{3} \left(\frac{2}{v_S^3} + \frac{1}{v_L^3} \right) \right]^{-\frac{1}{3}} \quad (5)$$

3. Results and Discussion

Figure 1 displays the SXRD patterns collected at $T = 600$ K and the Rietveld refinement results. The results suggest that the high-temperature measurements were successfully performed. In the refinement, tiny impurity phases of REF_3 were assumed [26]. The estimated lattice volume (V) is plotted in Fig. 2. By formula (2) and linear fitting in Fig. 2a–2e, β_V is estimated as 39.6, 32.9, 38.4, 37.8, and 36.4 (μK^{-1}) for $\text{LaO}_{0.5}\text{F}_{0.5}\text{BiS}_2$, $\text{CeO}_{0.5}\text{F}_{0.5}\text{BiS}_2$, $\text{PrO}_{0.5}\text{F}_{0.5}\text{BiS}_2$, $\text{NdO}_{0.5}\text{F}_{0.5}\text{BiS}_2$, and $\text{NdO}_{0.7}\text{F}_{0.3}\text{BiS}_2$, respectively.

The temperature dependences of the isotropic displacement parameters (U_{iso}) are plotted in Fig. 2g–2j. As mentioned in introduction, $\text{LaO}_{0.5}\text{F}_{0.5}\text{BiS}_2$ exhibits huge U_{iso} at the S1 site (see Fig. 2f), which is due to low in-plane chemical pressure [25,26]. The temperature dependence of U_{iso} for S1 is not remarkable, and the U_{iso} expected at $T = 0$ K is clearly large, which indicate the presence of static disorder at the S1 site. With increasing in-plane chemical pressure (by replacing La by Ce or Pr), U_{iso} at the S1 site is slightly suppressed. For RE = Nd, U_{iso} at the S1 site is clearly decreased and becomes lower than that at the Bi site. Furthermore, the U_{iso} at the S1 site is expected to approach zero at $T = 0$ K from the temperature dependence as shown in Fig. 2j, suggesting the suppression of in-plane static disorder in the superconducting sample with RE = Nd.

In Fig. 3a–3d, the T^2 dependence of C/T are displayed, and θ_D is estimated as 195, 197, 222, and 198 K for $\text{LaO}_{0.5}\text{F}_{0.5}\text{BiS}_2$, $\text{CeO}_{0.5}\text{F}_{0.5}\text{BiS}_2$, $\text{PrO}_{0.5}\text{F}_{0.5}\text{BiS}_2$, and $\text{NdO}_{0.7}\text{F}_{0.3}\text{BiS}_2$, respectively. The slightly larger θ_D for RE = Pr is consistent with a previous work [13]. $\theta_D = 189$ K for $\text{NdO}_{0.5}\text{F}_{0.5}\text{BiS}_2$ was calculated from a previous work [51].

The sound velocity (v_L) was measured and corrected using packing factor as described in Ref. 46. The estimated sound velocity parameters are listed in Table I. To estimate v_S and v_m ,

formulas (3–5) were used. In addition, bulk modulus (B) was calculated. B remarkably increases with decreasing lattice constant (increasing in-plane chemical pressure) from La to Nd as shown in Fig. 4. B is given by $B = -V_0(dP/dV)$, where V_0 is volume at initial state, and dP/dV corresponds to the change in internal pressure by the change in volume. Therefore, B shows how the material is resistant to compression. The results shown in Fig. 4 clearly indicate that in-plane chemical pressure modified the REOBiS₂-type structure, and the huge changes in structural characteristics should affect lattice vibration characters in the REO_{1-x}F_xBiS₂ system.

We estimated γ_G for the REO_{1-x}F_xBiS₂ samples to examine the evolution of anharmonicity by in-plane chemical pressure and the relationship with superconductivity. In addition, the influence of carrier doping amount is also discussed for RE = Pr and Nd. Figure 5(a) displays the T_c for REO_{0.5}F_{0.5}BiS₂ ($x = 0.5$) plotted as a function of RE³⁺ ionic radii [26]. In Fig. 5(b), the estimated γ_G is plotted. For γ_G ($x = 0.5$), the trend exhibits a correlation to that for T_c ; T_c increases with increasing γ_G . On the basis of previous studies on LaOBiS_{2-x}Se_x by INS [45] and γ_G [46], we assume that the increase in γ_G in REO_{1-x}F_xBiS₂ systems is also originating from the modified vibration of Bi along the c -axis [45].

On the effect of carrier concentration (x) on γ_G in REO_{1-x}F_xBiS₂, we observed a trend that γ_G for $x = 0.3$ is slightly smaller than that for $x = 0.5$ [Fig. 5(b)]. This difference would be due to the in-plane structural instability. As described in introduction, the in-plane local disorder in doped (F-substituted) REO_{1-x}F_xBiS₂ is suppressed by in-plane chemical pressure. However, the local disorder is remarkable in non-doped or low-carrier phases as suggested in Ref. 52. As a fact, the in-plane local disorder in REO_{1-x}F_xBiS₂ is suppressed by both F substitution and in-plane chemical pressure, and the anharmonic vibration is enhanced in less-disordered phases, namely in NdO_{0.5}F_{0.5}BiS₂.

We conclude that, with increasing in-plane chemical pressure, the anharmonic nature of the Bi vibration is enhanced, and T_c increases in the system. If the assumption is correct, we expect a higher T_c when the anharmonicity is further enhanced by applying a higher in-plane chemical pressure; for example, uniaxial strain on single crystals or strain effects in thin films would achieve such a situation. To clarify the nature of lattice vibration in REO_{1-x}F_xBiS₂ in detail, INS experiments are desired. In addition, further understanding of electronic states will be helpful for understanding the mechanisms of superconductivity in BiS₂-based systems because the enhancement of anharmonic nature generally enhances electron-phonon coupling [2]. Investigation on lattice anharmonicity in BiS₂-based systems will open new pathway to develop exotic superconductors where anharmonic vibration plays an essential role on pairing.

4. Conclusion

We have investigated Grüneisen parameter (γ_G) of $\text{REO}_{1-x}\text{F}_x\text{BiS}_2$ with different RE ions and carrier concentrations through the measurements of temperature-dependent XRD, sound velocity, and low-temperature specific heat (θ_D). With increasing in-plane chemical pressure, bulk modulus remarkably increases, and a high γ_G is observed for RE = Nd. The dependence of γ_G on in-plane chemical pressure exhibits a good correlation with T_c , and a higher T_c is achieved when γ_G is large for RE = Nd. In addition, γ_G shows a slight decrease by a decrease of F concentration (x) in $\text{REO}_{1-x}\text{F}_x\text{BiS}_2$. We propose that the anharmonic vibration of Bi along the c -axis observed in previous inelastic neutron scattering for thermoelectric $\text{LaOBiS}_{2-x}\text{Se}_x$ is present in $\text{REO}_{1-x}\text{F}_x\text{BiS}_2$, and the enhancement of the anharmonicity is positively linked to superconducting T_c and pairing mechanisms.

Acknowledgment

This work was partially funded by Grant-in-Aid for Scientific Research (KAKENHI) (No. 18KK0076) and Tokyo Metropolitan Government Advanced Research (No. H31-1).

*E-mail: mizugu@tmu.ac.jp

- 1) L. R. Testardi, Phys. Rev. B **5**, 4342 (1972).
- 2) Z. Hiroi, J. Yamaura, and K. Hattori, J. Phys. Soc. Jpn. **81**, 011012 (2012).
- 3) K. Oshiba and T. Hotta, J. Phys. Soc. Jpn. **80**, 094712 (2011).
- 4) A. Y. Liu, I. I. Mazin, and J. Kortus, Phys. Rev. Lett. **87**, 087005 (2001).
- 5) I. Errea, Matteo Calandra, C. J. Pickard, J. Nelson, R. J. Needs, Y. Li, H. Liu, Y. Zhang, Y. Ma, and F. Mauri, Phys. Rev. Lett. **114**, 157004 (2015).
- 6) T. Isono, D. Iguchi, T. Matsubara, Y. Machida, B. Salce, J. Flouquet, H. Ogusu, J. I. Yamaura, Z. Hiroi, and K. Izawa, J. Phys. Soc. Jpn. **82**, 114708 (2013).
- 7) B. Rousseau and A. Bergara, Phys. Rev. B **82**, 104504 (2010).
- 8) Y. Mizuguchi, H. Fujihisa, Y. Gotoh, K. Suzuki, H. Usui, K. Kuroki, S. Demura, Y. Takano, H. Izawa, and O. Miura, Phys. Rev. B **86**, 220510 (2012).
- 9) Y. Mizuguchi, S. Demura, K. Deguchi, Y. Takano, H. Fujihisa, Y. Gotoh, H. Izawa, and O. Miura, J. Phys. Soc. Jpn. **81**, 114725 (2012).

- 10) S. Demura, Y. Mizuguchi, K. Deguchi, H. Okazaki, H. Hara, T. Watanabe, S. J. Denholme, M. Fujioka, T. Ozaki, H. Fujihisa, Y. Gotoh, O. Miura, T. Yamaguchi, H. Takeya, and Y. Takano, *J. Phys. Soc. Jpn.* **82**, 033708 (2013).
- 11) J. Xing, S. Li, X. Ding, H. Yang, and H. H. Wen, *Phys. Rev. B* **86**, 214518 (2012).
- 12) S. Demura, K. Deguchi, Y. Mizuguchi, K. Sato, R. Honjyo, A. Yamashita, T. Yamaki, H. Hara, T. Watanabe, S. J. Denholme, M. Fujioka, H. Okazaki, T. Ozaki, O. Miura, T. Yamaguchi, H. Takeya, and Y. Takano, *J. Phys. Soc. Jpn.* **84**, 024709 (2015).
- 13) R. Jha, A. Kumar, S. K. Singh, V. P. S. Awana, *J. Supercond. Nov. Magn.* **26**, 499 (2012).
- 14) D. Yazici, K. Huang, B. D. White, A. H. Chang, A. J. Friedman, and M. B. Maple, *Philos. Mag.* **93**, 673 (2012).
- 15) X. Lin, X. Ni, B. Chen, X. Xu, X. Yang, J. Dai, Y. Li, X. Yang, Y. Luo, Q. Tao, G. Cao, and Z. Xu, *Phys. Rev. B* **87**, 020504 (2013).
- 16) H. F. Zhai, Z. T. Tang, H. Jiang, K. Xu, K. Zhang, P. Zhang, J. K. Bao, Y. L. Sun, W. H. Jiao, I. Nowik, I. Felner, Y. K. Li, X. F. Xu, Q. Tao, C. M. Feng, Z. A. Xu, and G. H. Cao, *Phys. Rev. B* **90**, 064518 (2014).
- 17) Y. Mizuguchi, *J. Phys. Soc. Jpn.* **88**, 041001 (2019).
- 18) H. F. Zhai, P. Zhang, and G. H. Cao, *J. Phys. Soc. Jpn.* **88**, 041003 (2019).
- 19) S. Iwasaki, Y. Kawai, S. Takahashi, T. Suda, Y. Wang, Y. Koshino, F. Ogura, Y. Shibayama, T. Kurosawa, M. Oda, M. Ido, and N. Momono, *J. Phys. Soc. Jpn.* **88**, 041005 (2019).
- 20) H. Usui, K. Suzuki, and K. Kuroki, *Phys. Rev. B* **86**, 220501 (2012).
- 21) H. Usui and K. Kuroki, *Nov. Supercond. Mater.* **1**, 50 (2015).
- 22) K. Terashima, J. Sonoyama, T. Wakita, M. Sunagawa, K. Ono, H. Kumigashira, T. Muro, M. Nagao, S. Watauchi, I. Tanaka, H. Okazaki, Y. Takano, O. Miura, Y. Mizuguchi, H. Usui, K. Suzuki, K. Kuroki, Y. Muraoka, and T. Yokoya, *Phys. Rev. B* **90**, 220512 (2014).
- 23) Y. Mizuguchi, T. Hiroi, J. Kajitani, H. Takatsu, H. Kadowaki, and O. Miura, *J. Phys. Soc. Jpn.* **83**, 053704 (2014).
- 24) J. Kajitani, T. Hiroi, A. Omachi, O. Miura, and Y. Mizuguchi, *J. Phys. Soc. Jpn.* **84**, 044712 (2015).
- 25) Y. Mizuguchi, A. Miura, J. Kajitani, T. Hiroi, O. Miura, K. Tadanaga, N. Kumada, E. Magome, C. Moriyoshi, and Y. Kuroiwa, *Sci. Rep.* **5**, 14968 (2015).
- 26) Y. Mizuguchi, K. Hoshi, Y. Goto, A. Miura, K. Tadanaga, C. Moriyoshi, and Y. Kuroiwa, *J. Phys. Soc. Jpn.* **87**, 023704 (2018).
- 27) Y. Mizuguchi, E. Paris, T. Sugimoto, A. Iadecola, J. Kajitani, O. Miura, T. Mizokawa, and

- N. L. Saini, *Phys. Chem. Chem. Phys.* **17**, 22090 (2015).
- 28) E. Paris, Y. Mizuguchi, M. Y. Hacısalihoglu, T. Hiroi, B. Joseph, G. Aquilanti, O. Miura, T. Mizokawa, and N. L. Saini, *J. Phys.: Condens. Matter* **29**, 145603 (2017)
- 29) A. Athauda, J. Yang, S. Lee, Y. Mizuguchi, K. Deguchi, Y. Takano, O. Miura, and D. Louca, *Phys. Rev. B* **91**, 144112 (2014)
- 30) A. Athauda and D. Louca, *J. Phys. Soc. Jpn.* **88**, 041004 (2019).
- 31) T. Yildirim, *Phys. Rev. B* **87**, 020506 (2013).
- 32) C. Morice, R. Akashi, T. Koretsune, S. S. Saxena, and R. Arita, *Phys. Rev. B* **95**, 180505 (2017).
- 33) K. Suzuki, H. Usui, K. Kuroki, T. Nomoto, K. Hattori, and H. Ikeda, *J. Phys. Soc. Jpn.* **88**, 041008 (2019).
- 34) J. Liu, D. Fang, Z. Wang, J. Xing, Z. Du, X. Zhu, H. Yang, and H. H. Wen, *EPL* **106**, 67002 (2014).
- 35) Y. Ota, K. Okazaki, H. Q. Yamamoto, T. Yamamoto, S. Watanabe, C. Chen, M. Nagao, S. Watauchi, I. Tanaka, Y. Takano, and S. Shin, *Phys. Rev. Lett.* **118**, 167002 (2017).
- 36) Y. C. Chan, K. Y. Yip, Y. W. Cheung, Y. T. Chan, Q. Niu, J. Kajitani, R. Higashinaka, T. D. Matsuda, Y. Yanase, Y. Aoki, K. T. Lai, and S. K. Goh, *Phys. Rev. B* **97**, 104509 (2018).
- 37) K. Hoshi and Y. Mizuguchi, *J. Phys.: Condens. Matter* **33**, 473001 (2021).
- 38) K. Hoshi, Y. Goto, and Y. Mizuguchi, *Phys. Rev. B* **97**, 094509 (2018).
- 39) R. Jha and Y. Mizuguchi, *Appl. Phys. Express* **13**, 093001 (2020).
- 40) K. Hoshi, M. Kimata, Y. Goto, T. D. Matsuda, and Y. Mizuguchi, *J. Phys. Soc. Jpn.* **88**, 033704 (2019).
- 41) K. Hoshi, M. Kimata, Y. Goto, A. Miura, C. Moriyoshi, Y. Kuroiwa, M. Nagao, and Y. Mizuguchi, *J. Phys. Commun.* **4**, 095028 (2020).
- 42) K. Hoshi, R. Kurihara, Y. Goto, M. Tokunaga, and Y. Mizuguchi, *Sci. Rep.* **12**, 288 (2022).
- 43) A. Nishida, O. Miura, C. H. Lee, and Y. Mizuguchi, *Appl. Phys. Express* **8**, 111801 (2015).
- 44) Y. Mizuguchi, A. Nishida, A. Omachi, and O. Miura, *Cogent Phys.* **3**, 1156281(1-14) (2016).
- 45) C. H. Lee, A. Nishida, T. Hasegawa, H. Nishiate, H. Kunioka, S. Ohira-Kawamura, M. Nakamura, K. Nakajima, and Y. Mizuguchi, *Appl. Phys. Lett.* **112**, 023903 (2018).
- 46) F. I. Abbas, A. Yamashita, K. Hoshi, R. Kiyama, Md. R. Kasem, Y. Goto, and Y. Mizuguchi, *Appl. Phys. Express* **14**, 071002 (2021).
- 47) S. Kawaguchi, M. Takemoto, K. Osaka, E. Nishibori, C. Moriyoshi, Y. Kubota, Y. Kuroiwa, and K. Sugimoto, *Rev. Sci. Instrum.* **88**, 085111 (2017).

- 48) F. Izumi and K. Momma, *Solid State Phenom.* **130**, 15 (2007).
- 49) K. Momma and F. Izumi, *J. Appl. Crystallogr.* **41**, 653 (2008).
- 50) F. I. Abbas, Y. Nakahira, A. Yamashita, Md. R. Kasem, M. Yoshida, Y. Goto, A. Miura, K. Terashima, R. Matsumoto, Y. Takano, C. Moriyoshi, and Y. Mizuguchi, arXiv:2202.12516.
- 51) R. Jha, A. Kumar, S. K. Singh, and V. P. S. Awana, *J. Appl. Phys.* **115**, 056102 (2013).
- 52) N. Hirayama, M. Ochi, and K. Kuroki, *Phys. Rev. B* **100**, 125201 (2019).

Table I. Parameters used for the estimation of γ_G .

RE	La	Ce	Pr	Nd	Nd
F contents (x)	0.5	0.5	0.5	0.5	0.3
Relative density (%)	100	100	97.8	96.0	94.9
β_V (μK^{-1})	39.6	32.9	38.4	37.8	36.4
v_L (exp) (m/s)	3330	3320	3450	3470	3450
v_L (ideal) (m/s)	3330	3320	3527	3616	3635
v_S (ideal) (m/s)	1689	1687	1875	1567	1640
v_m (ideal) (m/s)	1893	1890	2096	1770	1850
θ_D (K)	195	197	222	189 [51]	198
B (GPa)	43.2	44.3	49.8	65.6	64.5
C_V (J/K mol)	124.6	124.6	124.6	124.6	124.6
γ_G	0.99	0.82	1.03	1.29	1.22

Figures

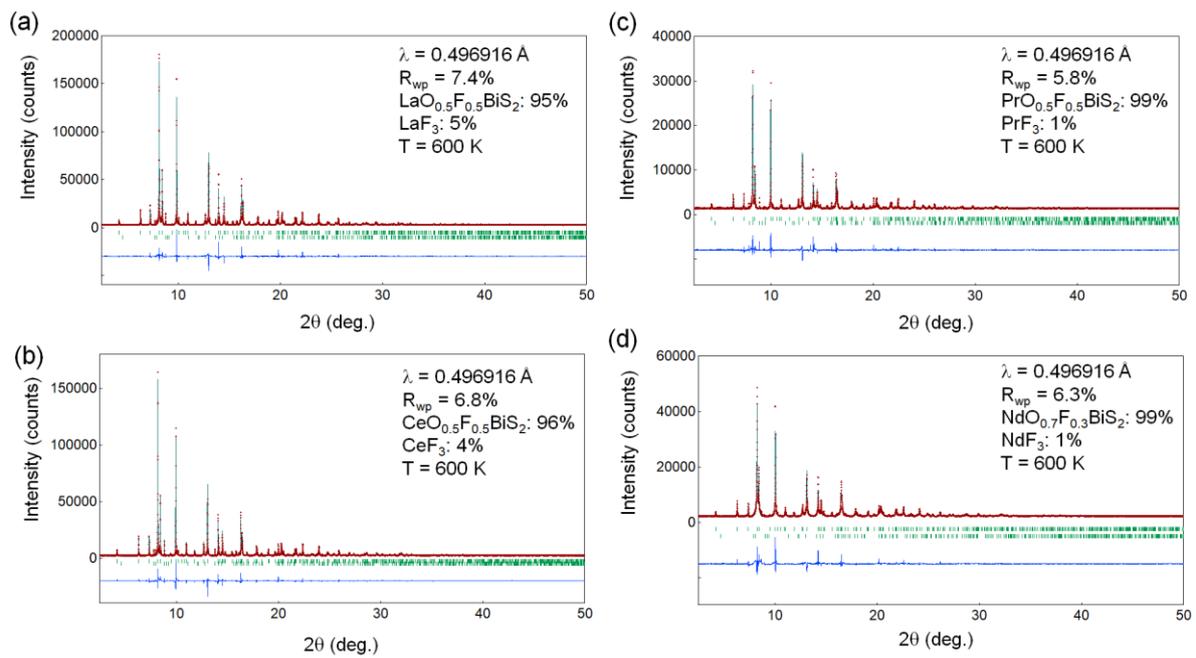


Fig. 1. SXRD patterns ($T = 600 \text{ K}$) and Rietveld refinement results for (a) $\text{LaO}_{0.5}\text{F}_{0.5}\text{BiS}_2$, (b) $\text{CeO}_{0.5}\text{F}_{0.5}\text{BiS}_2$, (c) $\text{PrO}_{0.5}\text{F}_{0.5}\text{BiS}_2$, and (d) $\text{NdO}_{0.7}\text{F}_{0.3}\text{BiS}_2$.

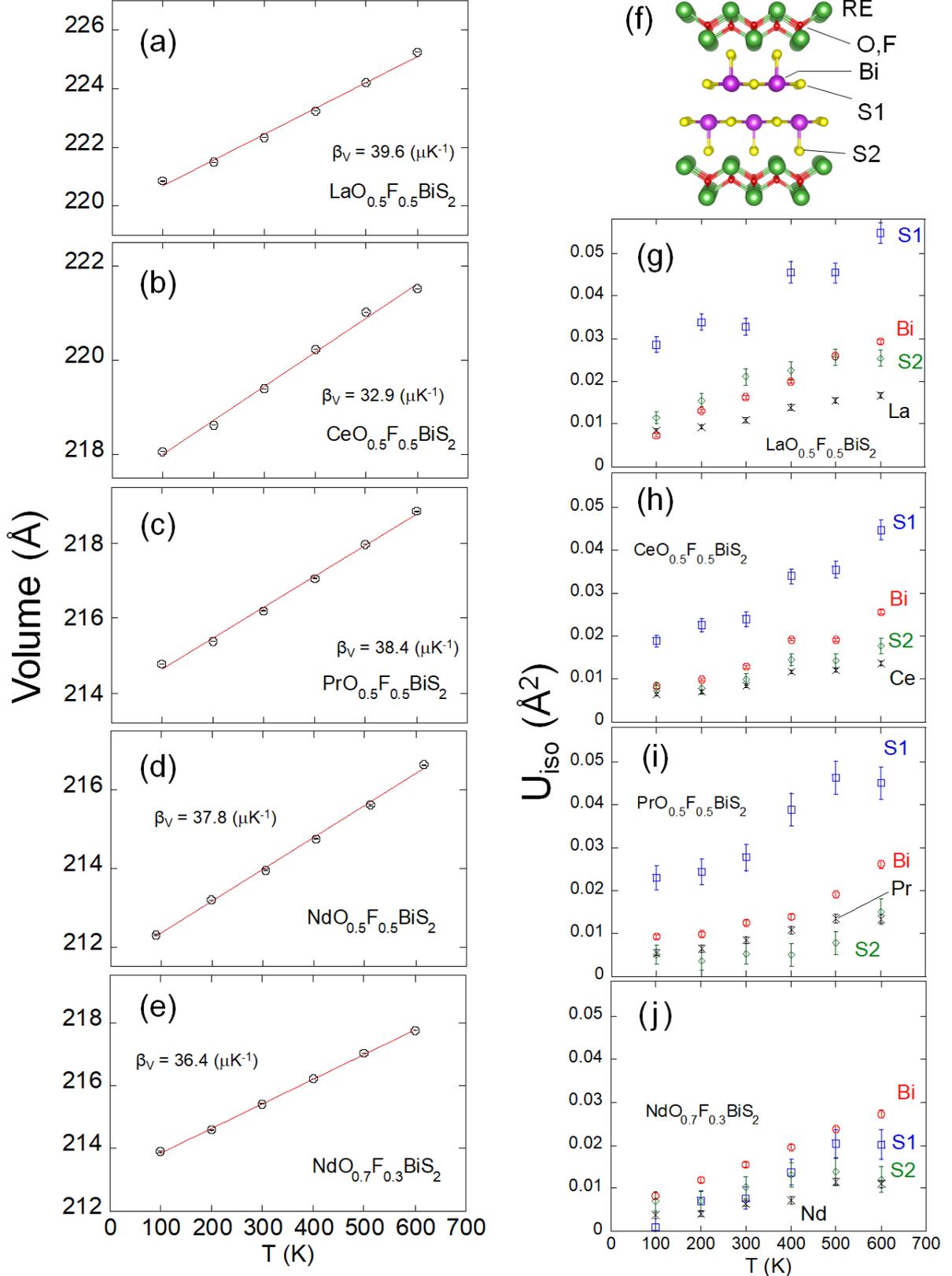


Fig. 2. Temperature dependence of lattice volume (V) for (a) LaO_{0.5}F_{0.5}BiS₂, (b) CeO_{0.5}F_{0.5}BiS₂, (c) PrO_{0.5}F_{0.5}BiS₂, (d) NdO_{0.5}F_{0.5}BiS₂, and (e) NdO_{0.7}F_{0.3}BiS₂. (f) Schematic image of crystal structure of RE(O,F)BiS₂. Temperature dependence of isotropic atomic displacement (U_{iso}) for (g) LaO_{0.5}F_{0.5}BiS₂, (h) CeO_{0.5}F_{0.5}BiS₂, (i) PrO_{0.5}F_{0.5}BiS₂, and (j) NdO_{0.7}F_{0.3}BiS₂.

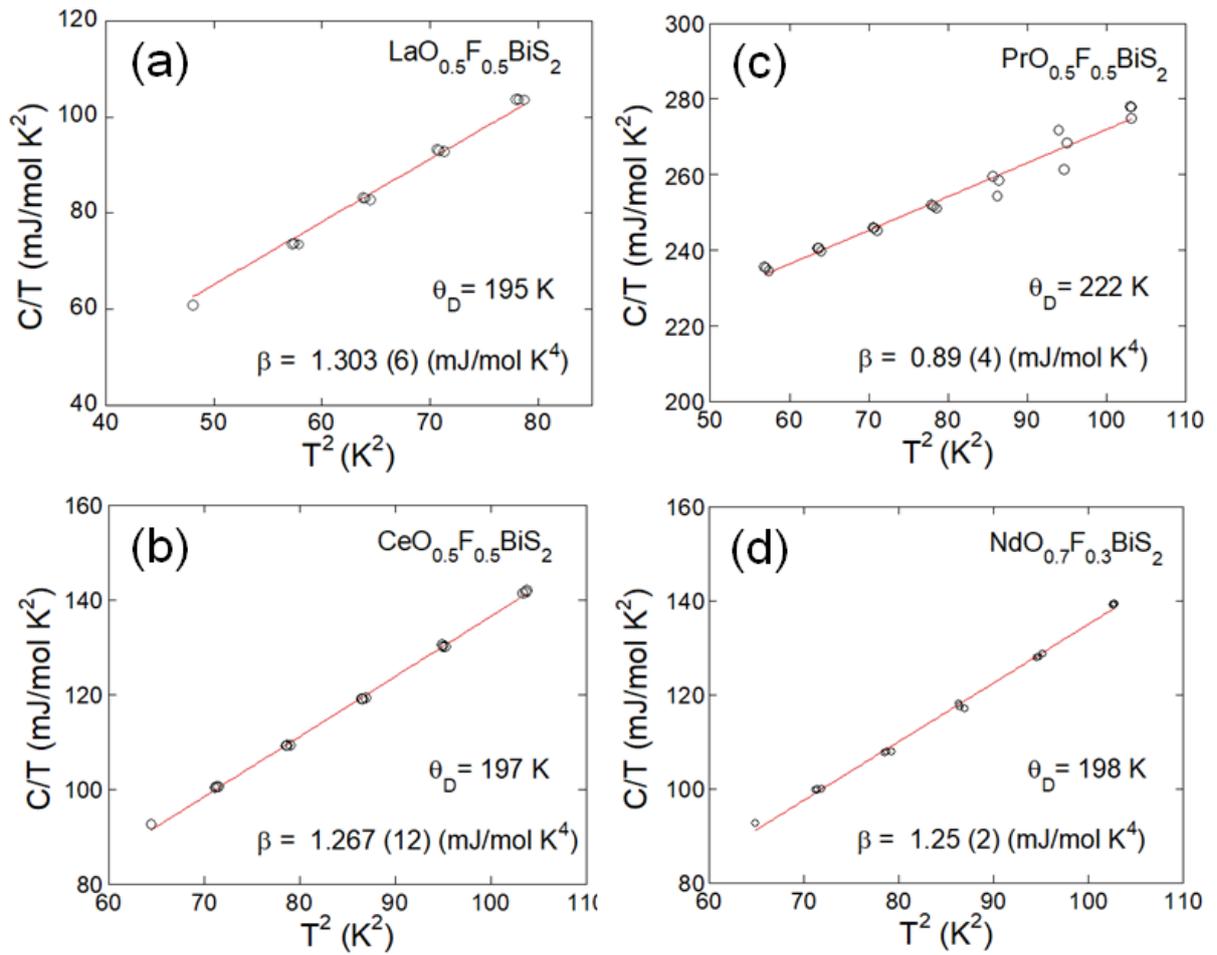


Fig. 3. T^2 dependence of C/T for (a) $\text{LaO}_{0.5}\text{F}_{0.5}\text{BiS}_2$, (b) $\text{CeO}_{0.5}\text{F}_{0.5}\text{BiS}_2$, (c) $\text{PrO}_{0.5}\text{F}_{0.5}\text{BiS}_2$, and (d) $\text{NdO}_{0.7}\text{F}_{0.3}\text{BiS}_2$.

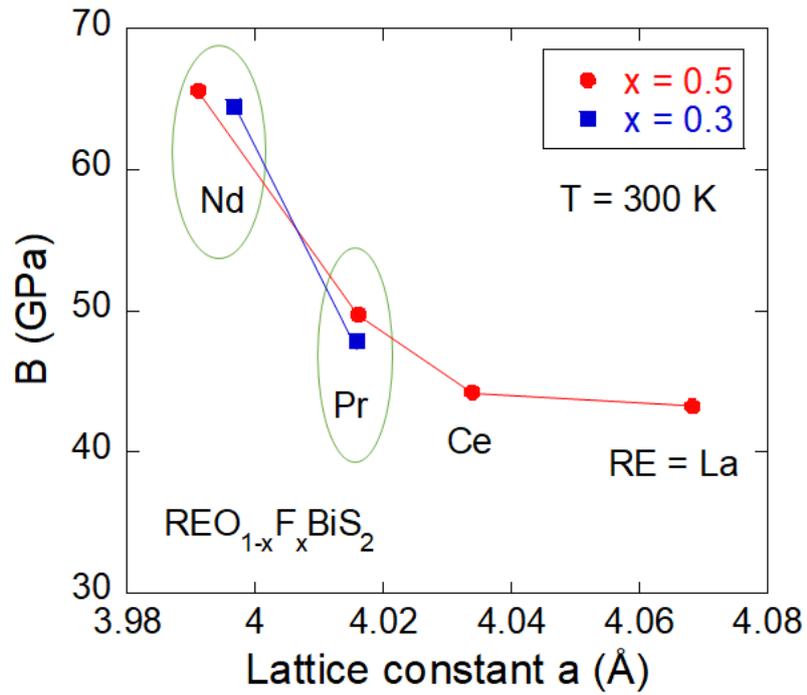


Fig. 4. Lattice constant ($T = 300$ K) dependence of bulk modulus (B). For $\text{REO}_{1-x}\text{F}_x\text{BiS}_2$, lattice constant a becomes a good measure of in-plane chemical pressure. B for $\text{PrO}_{0.7}\text{F}_{0.3}\text{BiS}_2$ has been reported in Ref. 50.

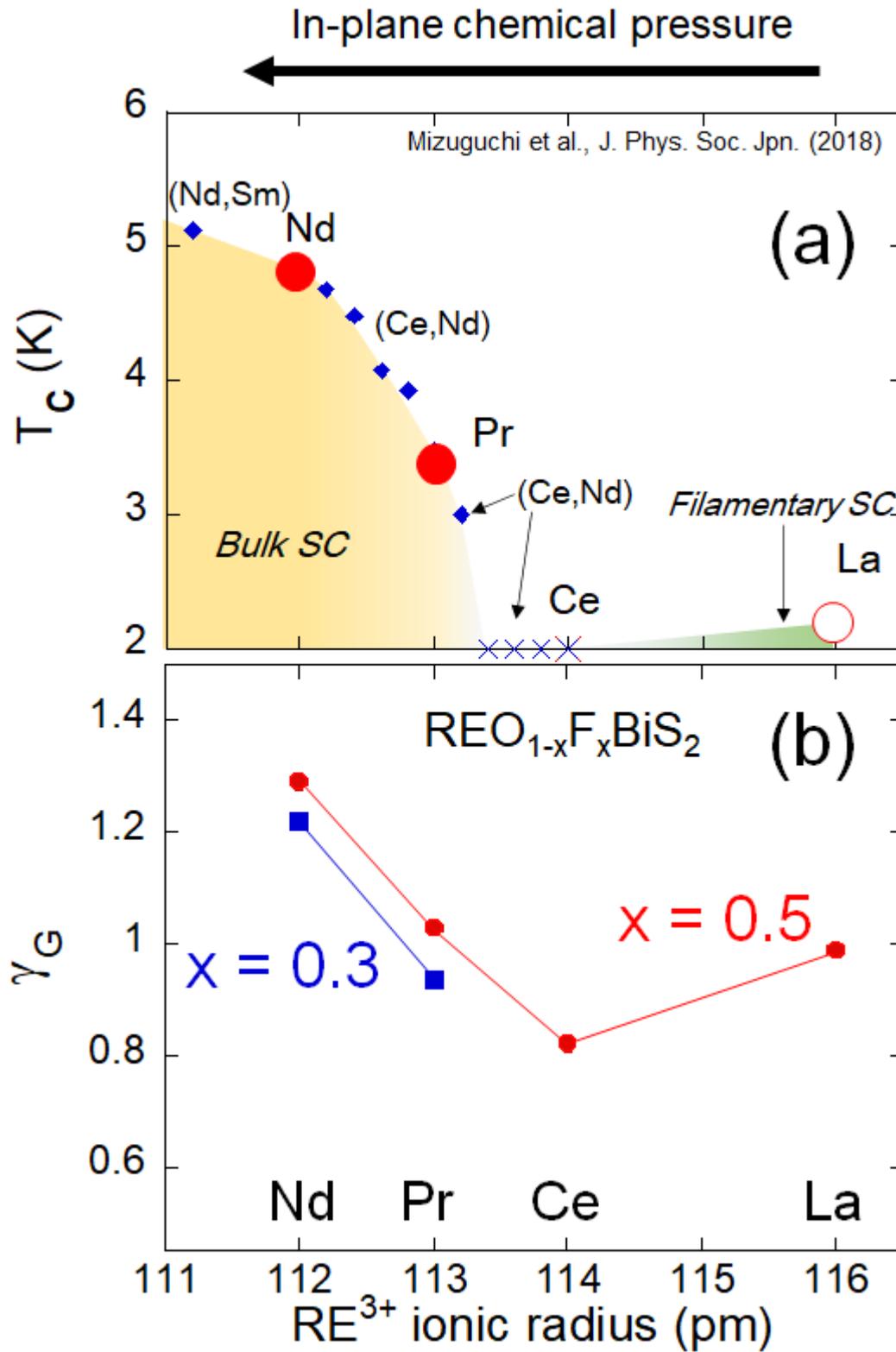


Fig. 5. RE^{3+} ionic radius dependence of (a) T_c for $REO_{0.5}F_{0.5}BiS_2$ ($x = 0.5$) (reproduced from Ref. 26) and (b) estimated γ_G for $REO_{1-x}F_xBiS_2$. In (a), cross symbols indicate that the compositions do not exhibit superconductivity at above 1.8 K.